Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	22	((epitaxial or epitaxially or epitaxy) near10 trench) same bulk same soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:02
L2	19	((epitaxial or epitaxially or epitaxy) near10 trench) with (bulk near (region or area or part or portion or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:05
L3	29	((epitaxial or epitaxially or epitaxy) near10 trench) near10 (bulk near2 (region or area or part or portion or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:07
L4	17	((epitaxial or epitaxially or epitaxy) near5 trench) near10 (bulk near2 (region or area or part or portion or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:07
L5	21	((epitaxial or epitaxially or epitaxy) near5 trench) with (bulk near2 (region or area or part or portion or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:07
L6	11	((epitaxial or epitaxially or epitaxy) near2 trench) with (bulk near2 (region or area or part or portion or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:08
L7	3	((epitaxial or epitaxially or epitaxy) near2 trench) with (bulk near2 (region or area or part or portion or layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:09
L8	1	((epitaxial or epitaxially or epitaxy) near2 trench) with (bulk near2 (region or area or part or portion or layer) with soi).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:09
L9	4	((epitaxial or epitaxially or epitaxy) near2 trench) with (bulk near2 (region or area or part or portion or layer) with soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:10

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L10	5	((epitaxial or epitaxially or epitaxy) near5 trench) with (bulk near2 (region or area or part or portion or layer) with soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:16
L11	11	((epitaxial or epitaxially or epitaxy) near5 trench) same (bulk near2 (region or area or part or portion or layer) same soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:21
L12	79	(bulk near2 region) with (between or boundary) with (soi near2 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:22
L13	67	(bulk near2 region) near5 (between or boundary) near5 (soi near2 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:23
L14	13	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:24
L15	12	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:26
L16	5	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler) with (epitaxy or epitaxial or epitaxially))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:27
L17	6	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler) with (semiconductor or silicon or epitaxy or epitaxial or epitaxially))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:27
L18	12	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler) with (semiconductor or silicon or polysilicon or epitaxy or epitaxial or epitaxially))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:27

L19	12	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler) near10 (semiconductor or silicon or polysilicon or epitaxy or epitaxial or epitaxially))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:29
L20	9	(bulk near2 region) near10 (between or boundary) near10 (soi near2 region) near10 trench and (trench near5 (fill or filling or filled or filler) near10 (semiconductor or silicon or polysilicon or epitaxy or epitaxial or epitaxially)) and (trench near10 sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:30

L37	8	I36 and ((epitaxy or epitaxial or epitaxially) near2 (fill or filling or filled or filler) near2 trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:32
L38	9	l36 and ((epitaxy or epitaxial or epitaxially) near5 (fill or filling or filled or filler) near5 trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:35
L39	38	l36 and ((epitaxy or epitaxial or epitaxially) near5 trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 13:35

L56	135	I55 and junction and (dope or doping or doped or dopant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 16:14
L57	72	l55 and (junction same (dope or doping or doped or dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 16:14
L58	10	I55 and (junction same (dope or doping or doped or dopant) same bulk)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 16:14
L59	5	I55 and (junction same (dope or doping or doped or dopant) same bulk same soi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 16:16
L60	4	I55 and (junction same (dope or doping or doped or dopant) same bulk same soi) and ((pn or p-n) near junction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/24 16:17